

ABSTRACT OF THE DISCLOSURE

A low-resistance ITO thin film having a resistivity on the order of, or lower than $10^{-4} \Omega \text{ cm}$, and a method for manufacturing such a film are disclosed. The ITO thin film is
5 manufactured by depositing ITO on a crystalline substrate by pulsed laser deposition, low-voltage sputtering, oxygen cluster beam deposition, chemical vapor deposition, metal organic chemical vapor deposition, metal organic chemical vapor deposition - atomic layer deposition, or molecule beam epitaxy.

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